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APT20SCD65K 650V 20A

Zero Recovery Silicon Carbide Schottky Diode

PRODUCT APPLICATIONS

- Anti-Parallel Diode

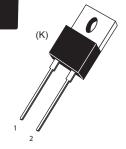
 Switchmode Power Supply
 Inverters
- Power Factor Correction (PFC)

PRODUCT FEATURES

- Zero Recovery Time (t_{rr})
- Popular TO-220 Package
- · Low Forward Voltage
- Low Leakage Current

PRODUCT BENEFITS

- Higher Reliability Systems
- Minimizes or eliminates snubber





- 1 Cathode 2 - Anode
 - Anode Back of Case - Cathode

MAXIMUM RATINGS

 $T_C = 25^{\circ}C$ unless otherwise specified.

Symbol	Characteristic / Test Conditions		Ratings	Unit	
V _R	Maximum D.C. Reverse Voltage				
V _{RRM}	Maximum Peak Repetitive Reverse Voltage		650	Volts	
V _{RWM}	Maximum Working Peak Reverse Voltage				
	Maximum D.C. Forward Current	T _C = 25°C	32		
l _F		T _c = 90°C	20		
I _{FRM}	Repetitive Peak Forward Surge Current (T _C = 25°C, t _p = 10ms, Half Sine Wave)		75	Amps	
I _{FSM}	Non-Repetitive Forward Surge Current (T _c = 25°C, t _p = 10ms, Half Sine)		165		
P _{тот}	Power Dissipation	T _C = 25°C	114	10/	
		T _C = 110°C	36	W	
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to 150	°C	
T _L	Lead Temperature for 10 Seconds		300		

STATIC ELECTRICAL CHARACTERISTICS

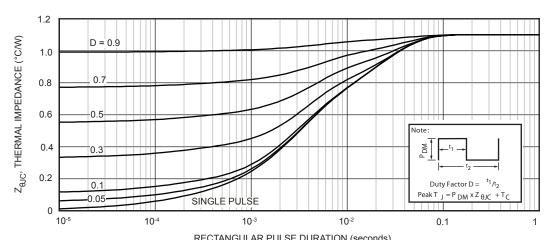
Symbol	Characteristic / Test Conditions		Min	Тур	Max	Unit
V _F	Forward Voltage	I _F = 20A T _J = 25°C		1.5	1.8	Volts
		I _F = 20A, T _J = 150°C		1.9		
I _{RM}	Maximum Reverse Leakage Current	V _R = 650V T _J = 25°C		20	400	μA
		V _R = 650V, T _J = 150°C		250		
Q _c	Total Capactive Charge V_R = 325V, I_F = 20A, di/dt = -500A/ μ s, T_J = 25°C			100		nC
C _T	Junction Capacitance $V_R = 0.1V$, $T_J = 25$ °C, $f = 1MHz$		680			
	Junction Capacitance V _R = 200V, T _J = 25°C, f = 1MHz			89		pF
	Junction Capacitance $V_R = 400V$, $T_J = 25$ °C, $f = 1MHz$			73		

THERMAL AND MECHANICAL CHARACTERISTICS

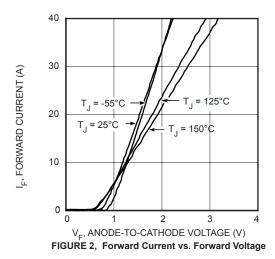
Symbol	Characteristic / Test Conditions	Min	Тур	Max	Unit
R _{eJC}	Junction-to-Case Thermal Resistance			1.1	°C/W
W _T	Package Weight		0.07		OZ
			1.9		g
Torque	Maximum Mounting Torque			6.4	lb∙in
				0.7	N·m

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES



RECTANGULAR PULSE DURATION (seconds)
FIGURE 1. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION



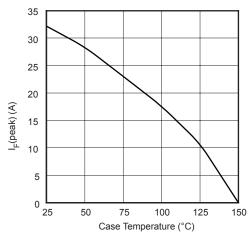


FIGURE 3, Maximum Forward Current vs. Case Temperature

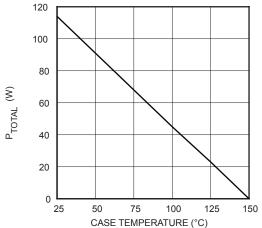


Figure 4. Maximum Power Dissipation vs. Case Temperature

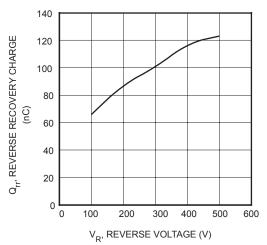


Figure 6. Reverse Recovery Charge vs. V_R

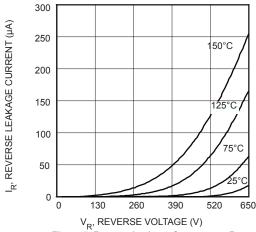
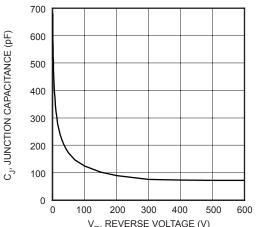


Figure 5. Reverse Leakage Currents vs. Reverse Voltage



 ${\rm V_{R}, REVERSE\ VOLTAGE\ (V)}$ Figure 7. Junction Capacitance vs. Reverse Voltage

TO-220 (K) Package Outline

e3 100% Sn 4° ~ 4.5° R0.5 [0.019] (2X) 4.320 [0.170] 4.570 [0.179] 10.000 [0.393] Cathode 1.140 [0.044] 10.360 [0.407] 1.400 [0.055] 2.650 [0.104] 3.050 [0.104] 6.295 [0.247] 6.795 [0.265] Ø3.71[0.146] 14.900 [0.586] 15.600 [0.614] Ø3.96 [0.155] 8.615 [0.339] 9.017 [0.355] 1.230 = 0.048 1.390 = 0.054 6.350 [0.250] 0.690 = 0.027 0.880 = 0.034 13.00 [0.511] 14.00 [0.551] Cathode Anode 2.500 [0.098] 2.740 [0.107] 2.590 [0.101] 5.130 [0.201]

Dimensions in millimeters and [inches]

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